

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07855 D T-33-11

2SD1069

SILICON NPN DOUBLE DIFFUSED TYPE (PCT PROCESS)

TV HORIZONTAL DEFLECTION OUTPUT APPLICATIONS.
HIGH VOLTAGE SWITCHING APPLICATIONS.

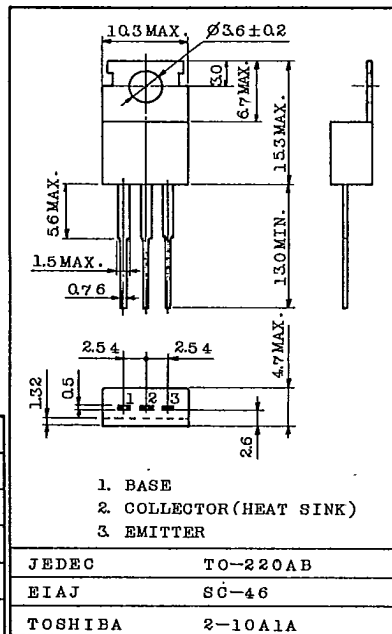
FEATURES:

- . Built in Damper Type.
- . High Collector Current Capability.
- . High Collector Power Dissipation Capability.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	300	V
Collector-Emitter Voltage	V _{CE0}	150	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current	I _C	7	A
Collector Current (Peak)	I _{CP}	15	A
Base Current	I _{BM}	2	A
Collector Power Dissipation	P _C	T _a =25°C	1.75
		T _c =25°C	40
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

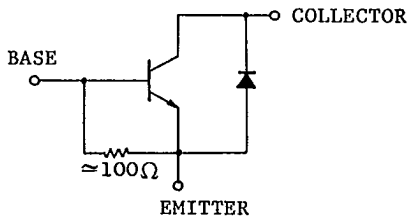
Unit in mm



Mounting kit No. AC75

Weight : 1.9 g

EQUIVALENT CIRCUIT



TOSHIBA CORPORATION

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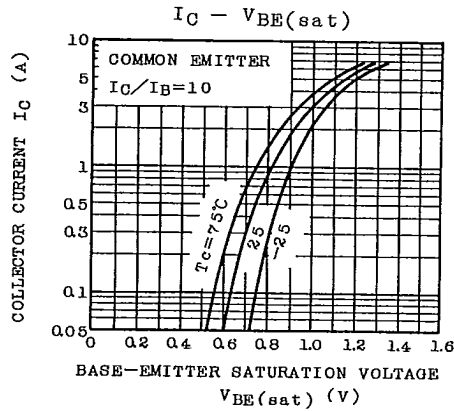
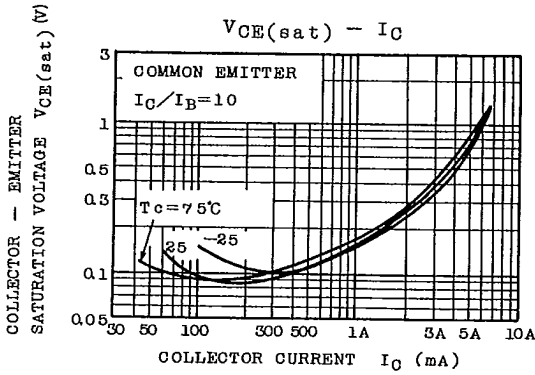
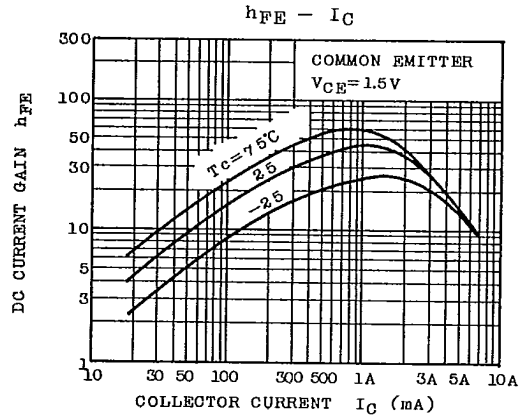
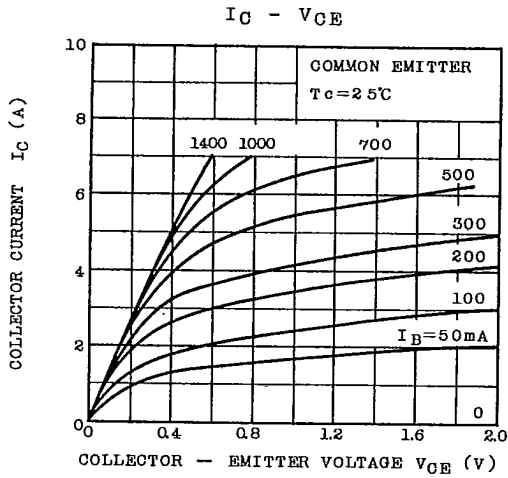
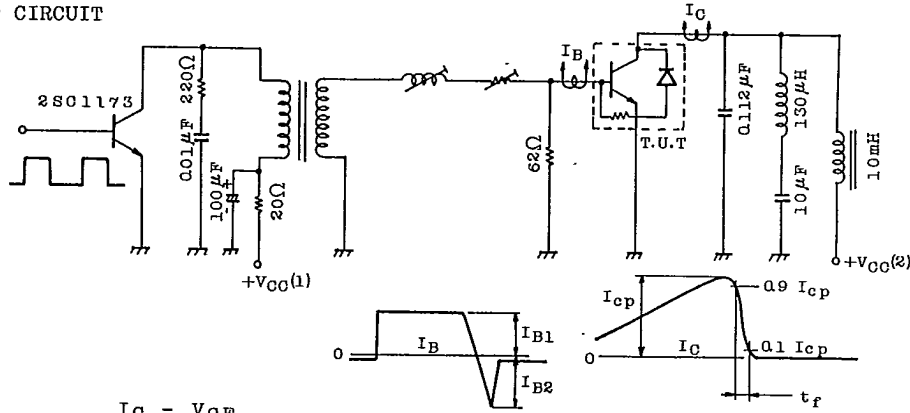
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICES	VCE=250V, VBE=0	-	-	1.0	mA
Collector-Emitter Sustaining Voltage	VCEO(SUS)	IC=0.1A, L=50mH	150	-	-	V
Collector-Base Breakdown Voltage	V(BR)CBO	IC=1mA, IE=0	300	-	-	V
Emitter-Base Breakdown Voltage	VEBO	IE=0.1A, IC=0	6	-	-	V
DC Forward Current Transfer Ratio	hFE	VCE=1.5V, IC=5A	10	-	-	
Collector-Emitter Saturation Voltage	VCE(sat)	IC=5A, IB=0.5A	-	-	1.5	V
Base-Emitter Saturation Voltage	VBE(sat)	IC=5A, IB=0.5A	-	-	1.5	V
Damper Diode Forward Voltage	-VF	IC=-6A	-	-	1.8	V
Collector Current Fall Time	tf	ICP=5A, IBI(end)=0.5A	-	-	1.0	μs
Transition Frequency	fT	VCE=10V, IC=0.2A	-	18	-	MHz

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TEST CIRCUIT



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This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.